



Docket No. 740819-000442

Serial No.: 09/692,211

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application of

Akihiko ISHIBASHI et al.

Serial No. 09/692,211

Filed: October 20, 2000

For: METHOD OF FABRICATING

NITRIDE SEMICONDUCTOR DEVICE

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) Art Unit: 2812

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) Examiner: S. MULPURI

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AMENDMENT UNDER 37 C.F.R. 1.111

Honorable Commissioner of Patents
Washington, D.C. 20231

November 27, 2001

Sir:

In response to the Office Action dated August 1, 2001, please amend the above-identified application and consider Applicants' remarks as follows:

IN THE CLAIMS:

Please amend claims 1 and 8 as follows.

1. (Amended) A method of fabricating a nitride semiconductor device by a vapor deposition method comprising:

plural steps of respectively growing plural nitride semiconductor layers on a substrate;
and

A 1
B 2
between a step of growing one nitride semiconductor layer and a step of growing another nitride semiconductor layer adjacent to said one nitride semiconductor layer among the plural steps, a step of changing a growth ambient pressure from a first growth ambient pressure to a second growth ambient pressure different from said first growth ambient pressure.

8. (Amended) A method of fabricating a nitride semiconductor device by a vapor deposition method comprising the steps of:

R 2
S 2
forming plural seed crystals on a substrate;